

Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM} / V_{RRM}	800/1200/1600	V
V_{TM}	1.55	V

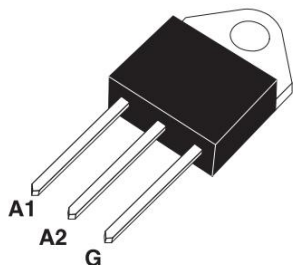
Feature

With high ability to withstand the shock loading of large current, With high commutation performances, 4 quadrants products especially recommended for use on inductive load.

Application

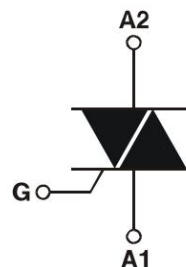
Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

Package

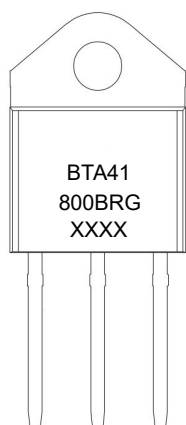


TO-3P Insulated

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	800/1200/1600	V
Repetitive peak reverse voltage	V_{RRM}	800/1200/1600	V
RMS on-state current	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	400	A
I^2t value for fusing (tp=10ms)	I^2t	880	A ² s
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	di/dt	50	A/ μ s
Peak gate current	I_{GM}	8	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Junction Temperature	T_J	-40 ~ +125	°C
Storage Temperature	T_{STG}	-40 ~ +150	°C

Electrical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition		Value		Unit
Gate trigger current	I_{GT}	$V_D = 12V$ $R_L = 100\Omega$	I-II-III	MAX.	50	mA
			IV	MAX.	120	mA
Gate trigger voltage	V_{GT}		ALL	MAX.	1.5	V
Gate non-trigger voltage	V_{GD}	$V_D = V_{DRM}$ $T_j = 125^\circ C$	ALL	MIN.	0.2	V
latching current	I_L	$I_G = 1.2I_{GT}$	I-II-III	MAX.	80	mA
			IV		160	
Holding current	I_H	$I_T = 500mA$		MAX.	80	mA
Critical-rate of rise of commutation voltage	dV/dt	$V_D = 2/3V_{DRM}$ Gate Open $T_j = 125^\circ C$		MIN.	500	V/ μs
STATIC CHARACTERISTICS						
Forward "on" voltage	V_{TM}	$I_{TM} = 60A$ $tp = 380\mu s$		MAX.	1.55	V
Repetitive Peak Off-State Current	I_{DRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^\circ C$	MAX.	10	μA
Repetitive Peak Reverse Current	I_{RRM}		$T_j = 125^\circ C$	MAX.	5	mA
THERMAL RESISTANCES						
Thermal resistance	$R_{th(j-c)}$	Junction to case(AC)		TYP.	0.9	$^\circ C/W$
	$R_{th(j-a)}$	Junction to ambient		TYP.	50	$^\circ C/W$

Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

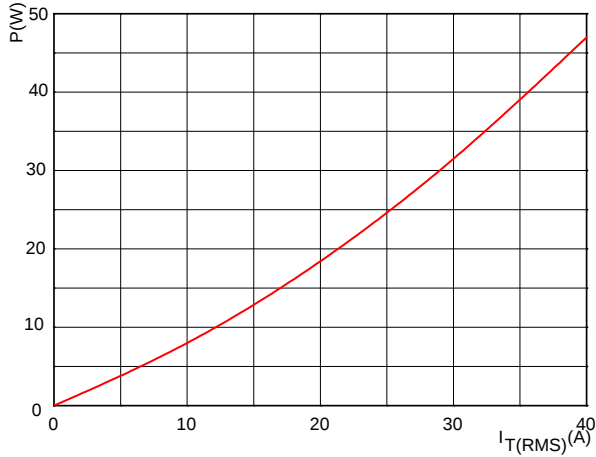


FIG.2: RMS on-state current versus case temperature (full cycle)

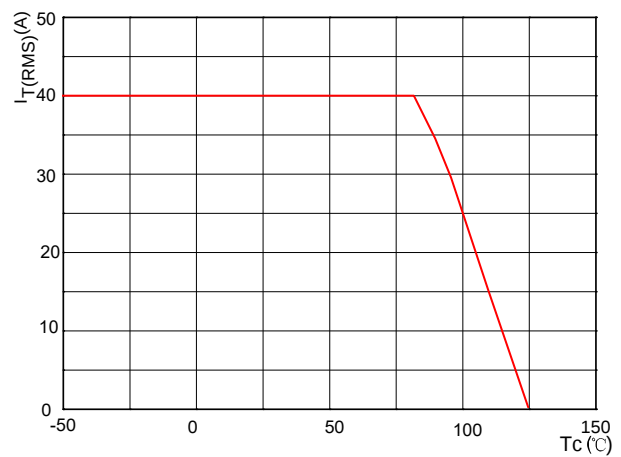


FIG.3: Surge peak on-state current versus number of cycles

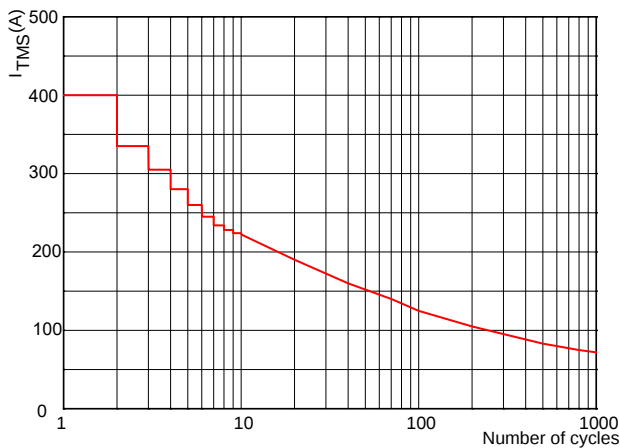


FIG.4: On-state characteristics (maximum values)

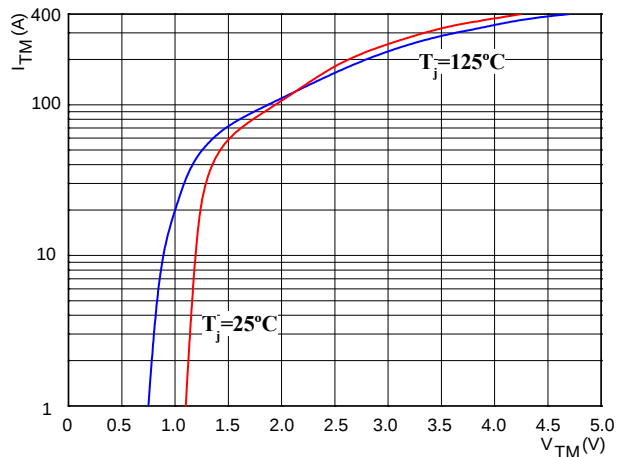


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$

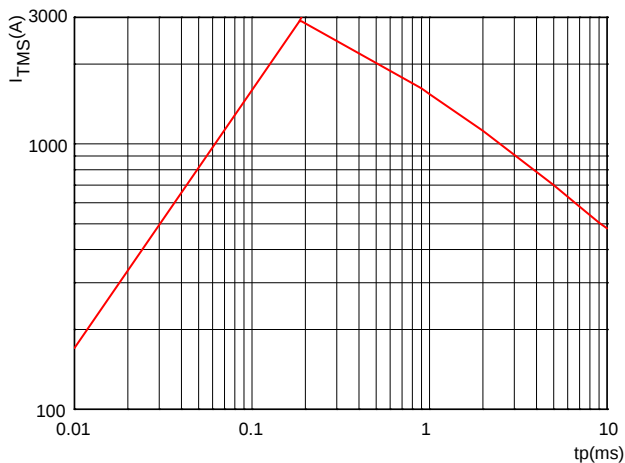
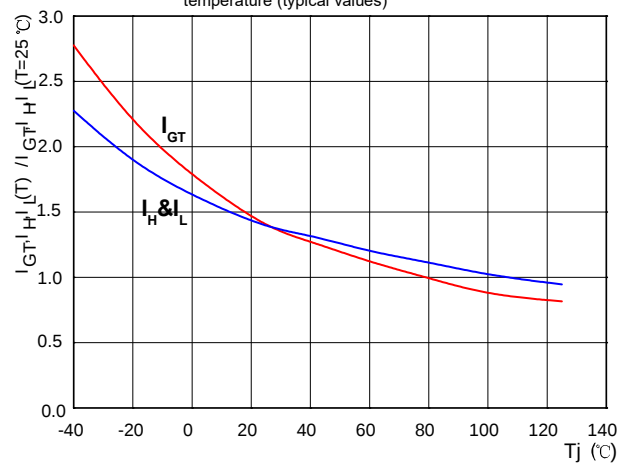


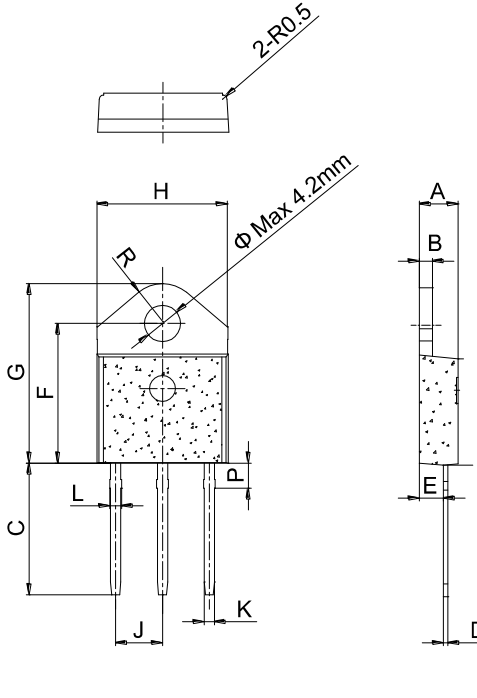
FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



Ordering Information

BT	A	41	—	800	BRG
Triacs	A: TO-3P Insulated				BRG: $I_{GT1-3} \leq 50\text{mA}$, $I_{GT4} \leq 120\text{mA}$
	$I_{T(RMS)}: 40\text{A}$				$800: V_{DRM} / V_{RRM} \geq 800\text{V}$ $1200: V_{DRM} / V_{RRM} \geq 1200\text{V}$ $1600: V_{DRM} / V_{RRM} \geq 1600\text{V}$

TO-3P Insulated Package Information

 The diagram shows a cross-section and a top view of the TO-3P insulated package. Key features include a central mounting hole with a diameter of 4.2mm maximum, a top flange with a 2-R0.5 fillet, and various dimensions labeled A through R. The package is designed for TO-3P insulated mounting.						
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	